

23 JUN 2005

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
22 July 2004 (22.07.2004)

PCT

(10) International Publication Number
WO 2004/060829 A1

- (51) International Patent Classification⁷: **C04B 35/20**
- (21) International Application Number:
PCT/JP2003/016559
- (22) International Filing Date:
24 December 2003 (24.12.2003)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
2002-380096 27 December 2002 (27.12.2002) JP
- (71) Applicant (for all designated States except US): **NIKKO COMPANY** [JP/JP]; 383, Ainoki-Machi, Matto-shi, Ishikawa-ken 924-8686 (JP).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): **KIDANI, Naoki** [JP/JP]; c/o Nikko Company, 383, Ainoki-Machi, Matto-shi, Ishikawa-ken 924-8686 (JP). **MIZUSHIMA, Kiyoshi** [JP/JP]; c/o Nikko Company, 383, Ainoki-Machi, Matto-shi, Ishikawa-ken 924-8686 (JP). **TAKIMOTO, Mikio** [JP/JP]; c/o Nikko Company, 383, Ainoki-Machi, Matto-shi, Ishikawa-ken 924-8686 (JP).
- (81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (regional): ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).
- Published:
— with international search report
- For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: LOW TEMPERATURE SINTERING CERAMIC COMPOSITION FOR USE IN HIGH FREQUENCY, METHOD OF FABRICATING THE SAME AND ELECTRONIC COMPONENT

(57) Abstract: A low temperature sintering ceramic composition that can be sintered at a temperature equal to or less than 1000 °C and has low dielectric constant and dielectric loss in a high frequency region of 17 GHz or more, an electronic component using the same and a method of fabricating the low temperature sintering ceramic are provided. The composition comprises MgO and SiO₂ in sum total in the range of from 64.0 to 99.2 % by mass; Bi₂O₃ in the range of from 0.4 to 33.0 % by mass; Li₂O in the range of from 0.4 to 3.0 % by mass; and MgO and SiO₂ are contained in the molar ratio of from 2: 1 to 2: 3.5, at least part thereof being contained as a complex oxide of Mg and Si.

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